

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 07-006993
(43)Date of publication of application : 10.01.1995

(51)Int.Cl. H01L 21/304

(21)Application number : 05-321478 (71)Applicant : GOLD STAR ELECTRON CO LTD
(22)Date of filing : 21.12.1993 (72)Inventor : LEE CHANG-JAE
KIM HYEUNG-TAE

(30)Priority

Priority number : 92 9225455 Priority date : 24.12.1992 Priority country : KR

(54) PROCESS FOR CLEANING SEMICONDUCTOR DEVICES

(57)Abstract:

PURPOSE: To maintain an appropriate impurity concentration by removing Cu ions and to allow a highly durable, high-performance cleaning to be effected by placing semiconductor devices in a cleaning vessel which contains an HF solution and supplying an O₃ gas into the vessel.

CONSTITUTION: Semiconductor devices 10 to be cleaned are placed in a cleaning vessel 11 containing an HF solution 12, and an O₃ gas is supplied into the vessel 11 by foaming the gas. The O₃ gas is supplied via a tube 13 that has on its distal end a plurality of golf ball-shaped nozzles 14, each nozzle having a plurality of holes 16. The O₃ gas supplied via the tube 13 is changed into O₂ and [O], and the [O] either is dissolved into the HF solution or oxidizes an impurity metal (Cu) present in a surface of a Si crystal, thereby forming chemically stable CuF₂ precipitates. By thereafter removing the CuF₂ precipitates using an ultraclean distilled water, the surfaces of the semiconductor devices can be cleaned.

